業績目録（末光眞希）

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薄膜 · 表面界面物性, 応用物性 · 結晶工学, 電子 · 電気材料工学

研究課題

・ Si 系半導体薄膜のガスソース分子線エピタキシー法による成長
・ Si 基板上グラフェンとデバイス

学内活動

記念会館運営構想委員会	2006年12月 ー 2008年3月
学友会文化部長	2008年4月 ー 2018年3月
東北大学ホームカミングデー記念コンサート実行委員長	2009年4月 ー 現在
電気通信研究所国際化推進室会議委員長	2011年2月 ー 現在
百周年記念会館副館長	2012年4月 ー 現在
電気通信研究所ナノ · スピン実験施設長	2017年4月 ー 2018年3月

学術受賞

第３０回熊谷記念真空科学論文賞 [日本真空協会]	2005年
2011 年度 APEX/JJAP 編集貢献賞 [応用物理学会欧文誌刊行委員会]	2011年
平成 23 年度日本表面科学会論文賞 [日本表面科学会]	2011年
IAAM メダル [IAAM]	2016年
応物フェロー [応用物理学会]	2017年

著書

1) 半導体評価事典（執筆担当部分）NMR. [(1994)]

末光　眞希

2) フッ素化学が拓くプロセスイノベーション（執筆担当部分）HF/UVOC クリーニング. [(1995)]

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3) 量子力学基礎（執筆担当部分）第１ ～ 第５章. [朝倉書店, (2007)1 月]

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